

	Type	Hits	Search Text	DBs
1	BRS	1	10/731018	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
2	BRS	1	functional ADJ film and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS	1717	349/113	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS	1772	349/43	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
5	BRS	757	349/38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	BRS	42	S3 and S4 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	BRS	1	10/731018	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	BRS	4	light ADJ (shield\$3 block\$3) ADJ insulat\$3 ADJ (layer film) with (SiN silicon ADJ nitride SiON silicon ADJ oxide ADJ nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
9	BRS	4	light ADJ (shield\$3 block\$3) ADJ insulat\$3 ADJ (layer film) same (SiN silicon ADJ nitride SiON silicon ADJ oxide ADJ nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	BRS	1119	light ADJ (shield\$3 block\$3) same (SiN silicon ADJ nitride SiON silicon ADJ oxide ADJ nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	BRS	492	light ADJ (shield\$3 block\$3) with (SiN silicon ADJ nitride SiON silicon ADJ oxide ADJ nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	BRS	1976	large ADJ dielectric ADJ constant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
13	BRS	16	S11 and S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	BRS	1	10/731018 and via ADJ hole	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB